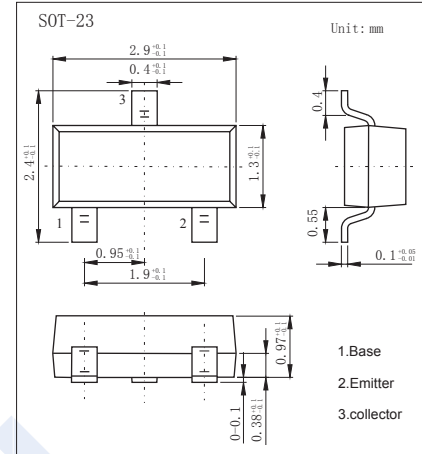


NPN Transistors

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■ Features

- Collector Current Capability $I_C=500\text{mA}$
- Collector Emitter Voltage $V_{CE0}=20\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	50	V
Collector - Emitter Voltage	V_{CEO}	20	
Emitter - Base Voltage	V_{EBO}	25	
Collector Current - Continuous	I_C	500	mA
Collector Current - Pulse	I_{CP}	800	
Base Current	I_B	100	
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	50			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{mA}, I_B = 0$	20			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	25			
Collector-base cut-off current	I_{CBO}	$V_{CB}=40 \text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 20\text{V}, I_C=0$			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=2\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=2\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE}= 5\text{V}, I_C= 10\text{mA}$	300		1200	
Turn-on time	t_{on}	See specified test circuit		135		ns
Storage time	t_{stg}			450		
Turn-off time	t_{off}			100		
Collector output capacitance	C_{ob}	$V_{CB}= 10\text{V}, f=1\text{MHz}$		3.6		pF
Transition frequency	f_T	$V_{CE}= 10\text{V}, I_C=10\text{mA}$		250		MHz

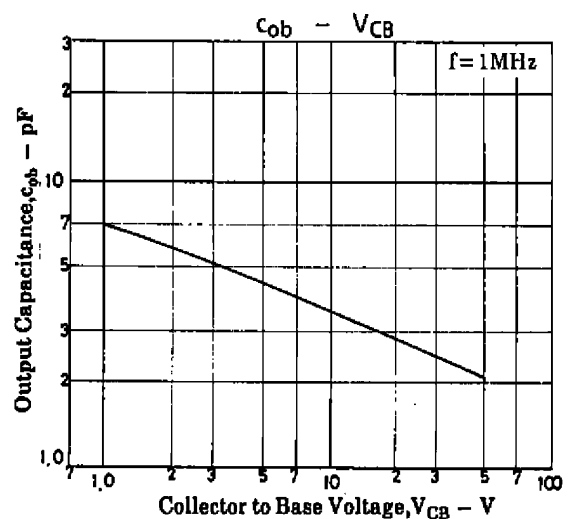
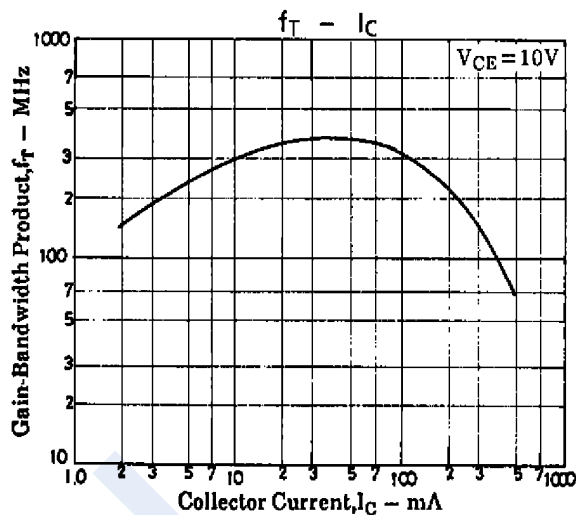
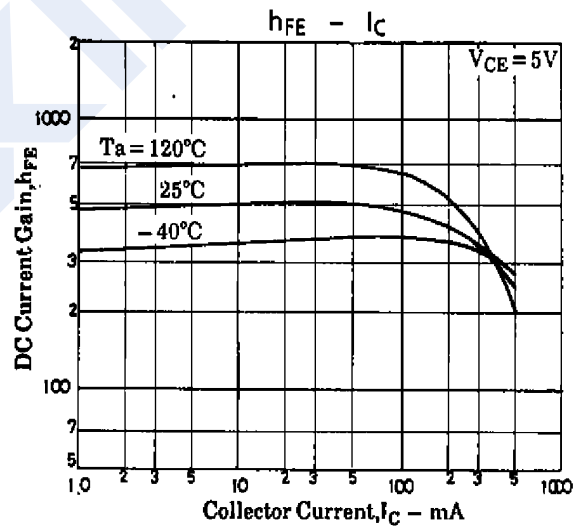
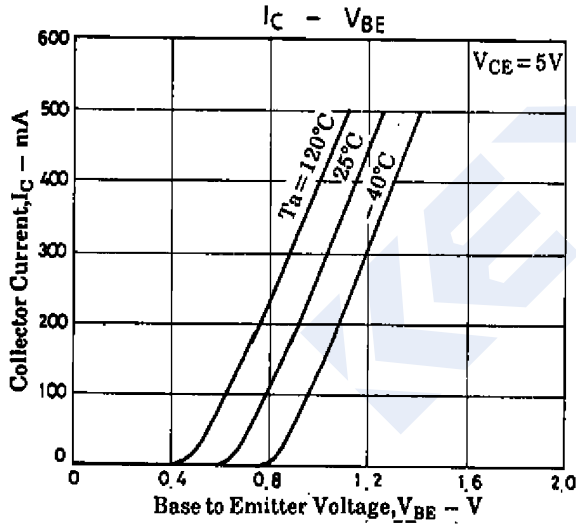
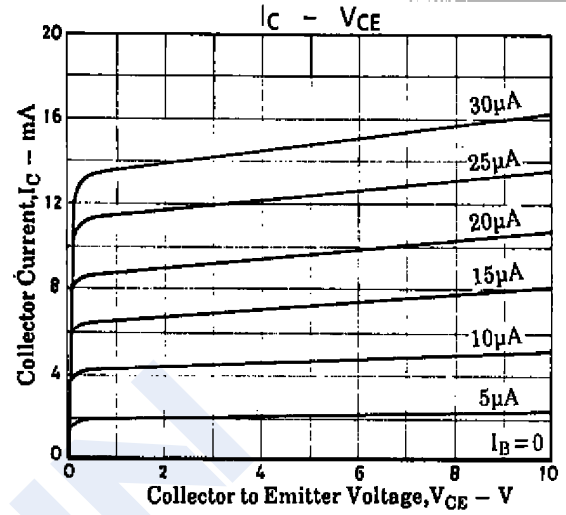
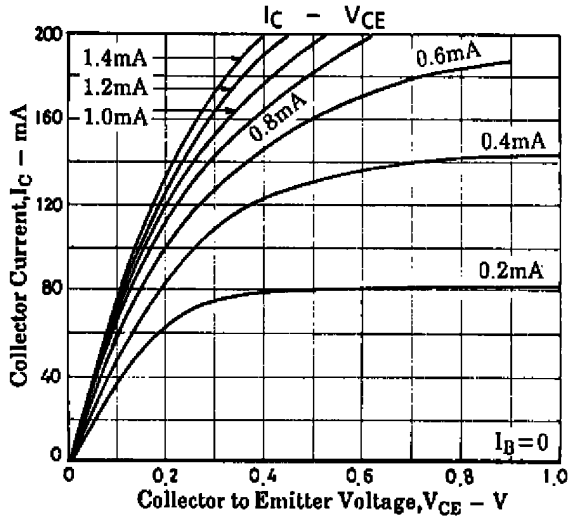
■ Marking

Marking	WT
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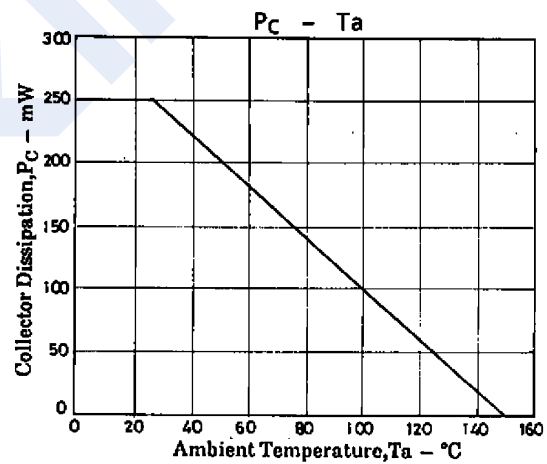
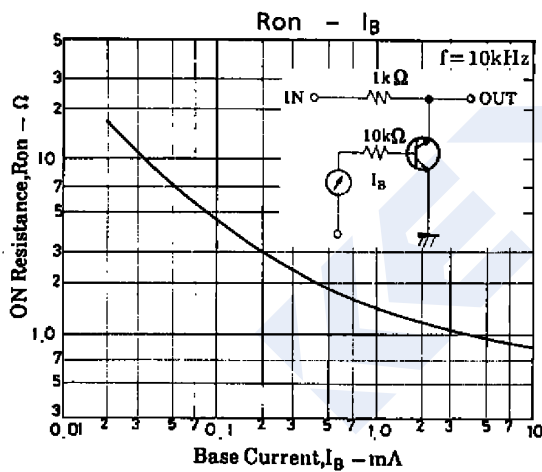
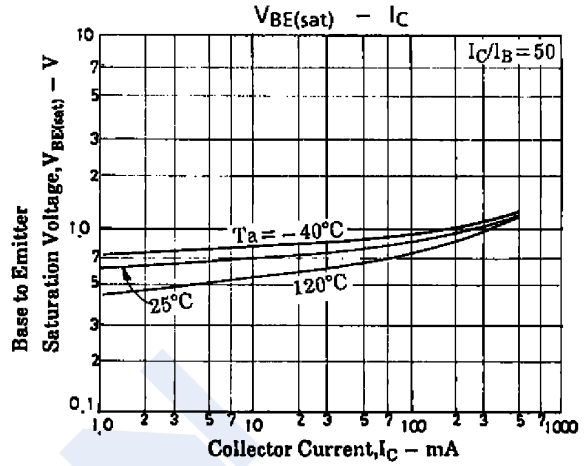
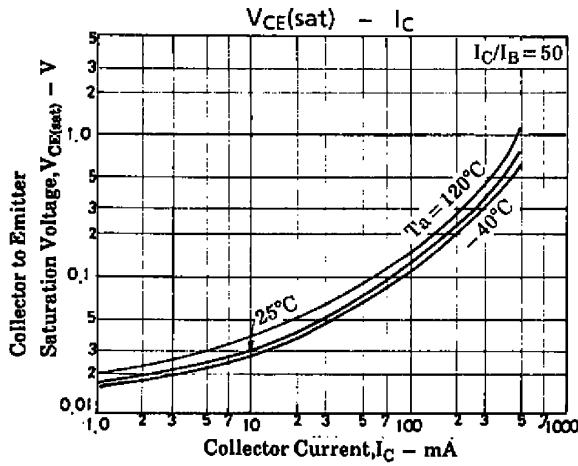
■ Typical Characteristics



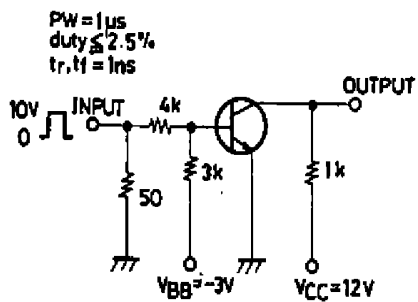
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■ Typical Characteristics



Switching Time Test Circuit



Unit (Resistance : Ω)